

*Advance Information*

**TRIACS**

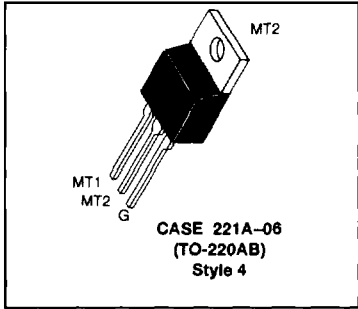
**Silicon Bidirectional Thyristors**

Designed for high performance full-wave ac control applications where high noise immunity and commutating di/dt are required.

- Blocking Voltage to 800 Volts
- On-State Current Rating of 12 Amperes RMS at 70°C
- Uniform Gate Trigger currents in Three Modes
- High Immunity to dv/dt — 250 V/μs minimum at 125°C
- High Commutating di/dt — 6.5 A/ms minimum at 125°C
- Industry Standard TO-220 AB Package
- High Surge Current Capability — 120 Amperes

**MAC12  
SERIES\***  
\*Motorola preferred devices

**TRIACS  
12 AMPERES RMS  
400 thru 800  
VOLTS**



**MAXIMUM RATINGS** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (1) ( $T_J = -40$ to $125^\circ\text{C}$ , Sine Wave, 50 to 60 Hz, Gate Open)	$V_{DRM}$	400 600 800	Volts
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_C = 70^\circ\text{C}$ )	$I_T(\text{RMS})$	12	A
Peak Non-repetitive Surge Current (One Full Cycle, 60 Hz, $T_J = 125^\circ\text{C}$ )	$I_{TSM}$	100	A
Circuit Fusing Consideration ( $t = 8.3$ ms)	$I^2t$	41	$\text{A}^2\text{sec}$
Peak Gate Power (Pulse Width $\leq 1.0$ μs, $T_C = 80^\circ\text{C}$ )	$P_{GM}$	16	Watts
Average Gate Power ( $t = 8.3$ ms, $T_C = 80^\circ\text{C}$ )	$P_{G(AV)}$	0.35	Watts
Operating Junction Temperature Range	$T_J$	-40 to +125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-40 to +150	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

Thermal Resistance — Junction to Case	$R_{\theta JC}$	2.2	$^\circ\text{C/W}$
— Junction to Ambient	$R_{\theta JA}$	62.5	
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	$T_L$	260	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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**OFF CHARACTERISTICS**

Peak Repetitive Blocking Current ( $V_D = \text{Rated } V_{DRM}$ , Gate Open)	$I_{DRM}$	—	—	0.01 2.0	mA
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(1)  $V_{DRM}$  and  $V_{RRM}$  for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

This document contains information on a new product. Specifications and information herein are subject to change without notice.

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 1

## MAC12 SERIES

### ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>ON CHARACTERISTICS</b>					
Peak On-State Voltage* ( $I_{TM} = \pm 17\text{ A}$ )	$V_{TM}$	—	—	1.85	Volts
Continuous Gate Trigger Current ( $V_D = 12\text{ V}$ , $R_L = 100\ \Omega$ )	$I_{GT}$	5.0	13	35	mA
MT2(+), G(+)		5.0	16	35	
MT2(+), G(-)		5.0	18	35	
Hold Current ( $V_D = 12\text{ V}$ , Gate Open, Initiating Current = $\pm 150\text{ mA}$ )	$I_H$	—	20	40	mA
Latch Current ( $V_D = 24\text{ V}$ , $I_G = 35\text{ mA}$ )	$I_L$	—	20	50	mA
MT2(+), G(+); MT2(-), G(-)		—	30	80	
Gate Trigger Voltage ( $V_D = 12\text{ V}$ , $R_L = 100\ \Omega$ )	$V_{GT}$	0.5	0.69	1.5	Volts
MT2(+), G(+)		0.5	0.77	1.5	
MT2(+), G(-)		0.5	0.72	1.5	
<b>DYNAMIC CHARACTERISTICS</b>					
Rate of Change of Commutating Current* ( $V_D = 400\text{ V}$ , $I_{TM} = 4.4\text{ A}$ , Commutating $dv/dt = 18\text{ V}/\mu\text{s}$ , Gate Open, $T_J = 125^\circ\text{C}$ , $f = 250\text{ Hz}$ , No Snubber)	$(dv/dt)_c$	6.5	—	—	A/ms
Critical Rate of Rise of Off-State Voltage ( $V_D = \text{Rated } V_{DRM}$ , Exponential Waveform, Gate Open, $T_J = 125^\circ\text{C}$ )	$dv/dt$	250	—	—	$\text{V}/\mu\text{s}$

\*Indicates Pulse Test: Pulse Width  $\leq 2.0\text{ ms}$ , Duty Cycle  $\leq 2\%$ .